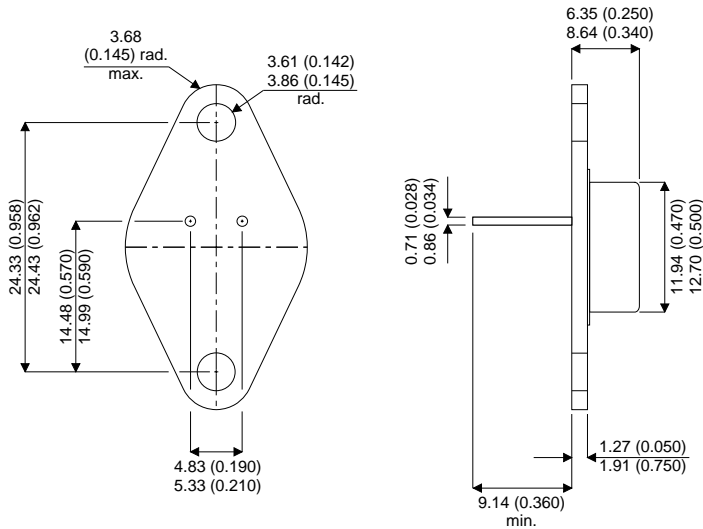


MECHANICAL DATA

Dimensions in mm



TO66 Package.

Pin 1 – Base Pin 2 – Emitter Case - Collector

**PNP
SILICON TRANSISTOR,
EPITAXIAL BASE**

FEATURES:

- LF Large Signal Power Amplification
- Medium Current Switching

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{CBO}	Collector – Base Voltage (Open Emitter)	- 90V
V_{CEO}	Collector – Emitter Voltage (Open Base)	- 55V
V_{CER}	Collector – Emitter Voltage $R_{BE} = 100\Omega$	- 60V
V_{CEX}	Collector – Base Voltage $V_{BE} = +1.5V$	- 90V
V_{EBO}	Emitter – Base Voltage	-7V
I_C	Collector Current	-4V
I_B	Base Current	-2V
P_{tot}	Power Dissipation	29W
T_J	Maximum Junction Temperature	200°C
T_{STG}	Storage Temperature	-65 to 200°C
$R_{th-(j-c)}$	Junction to Case.	6°C / W

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CEX} Collector Emitter Cut Off Current	$V_{CE} = -90V$ $V_{BE} = +1.5V$			-1	mA
	$V_{CE} = -30V$ $V_{BE} = +1.5V$ $T_{case} = 150^{\circ}C$			-5	
$V_{CEO(SUS)}$ * Collector Emitter Breakdown Voltage	$I_C = -100mA$ $I_B = 0$	-55			V
$V_{CER(SUS)}$ * Collector Emitter Breakdown Voltage	$I_C = -100mA$ $R_{BE} = 100\Omega$	-60			
$V_{(BR)EBO}$ * Emitter Base Breakdown Voltage	$I_E = -1A$ $I_C = 0$	-7			V
h_{21E} * Static Forward Current Transfer Ratio	$V_{CE} = -4V$ $I_C = -0.5A$	25		250	—
$V_{CE(sat)}$ * Collector Emitter Saturation Voltage	$I_C = -0.5A$ $I_B = -0.05A$			-1	V
V_{BE} * Base Emitter Voltage	$V_{CE} = -4V$ $I_C = -0.5A$			-1.7	V
f_T Transition Frequency	$V_{CB} = -10V$ $I_C = -0.2A$ $f = 1MHz$	4			MHz

* Pulse test $t_p = 300\mu s$, $\delta < 2\%$